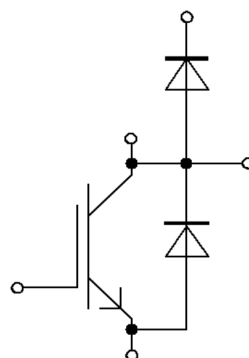


62mm C-Series 模块 采用第三代沟槽栅/场终止IGBT3和第三代发射极控制二极管
62mm C-Series module with Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode

初步数据 / Preliminary Data



$V_{CES} = 600V$

$I_{C\ nom} = 300A / I_{CRM} = 600A$

潜在应用

- 三电平应用
- 斩波应用

电气特性

- $T_{vj\ op} = 150^{\circ}C$
- 无与伦比的坚固性
- 沟槽栅IGBT3

机械特性

- 2.5 kV 交流 1分钟 绝缘
- 封装的 CTI > 400
- 标准封装
- 绝缘的基板

Potential Applications

- 3-level-applications
- Chopper applications

Electrical Features

- $T_{vj\ op} = 150^{\circ}C$
- Unbeatable robustness
- Trench IGBT 3

Mechanical Features

- 2.5 kV AC 1min insulation
- Package with CTI > 400
- Standard housing
- Isolated base plate

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

初步数据 Preliminary Data

IGBT, 制动-斩波器 / IGBT, Brake-Chopper

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	600	V
连续集电极直流电流 Continuous DC collector current	$T_C = 70^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	I_{CDC}	300	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	600	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,45 1,60 1,70	1,90	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 12,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	4,90	5,80	6,50 V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}$		Q_G	3,20		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,0		Ω
输入电容 Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	19,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,57		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 300\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,11 0,12 0,13		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 300\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,05 0,06 0,06		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 300\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,49 0,52 0,53		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 300\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,05 0,07 0,07		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 300\text{ A}, V_{CE} = 300\text{ V}, L\sigma = 30\text{ nH}$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	3,10 3,30		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 300\text{ A}, V_{CE} = 300\text{ V}, L\sigma = 30\text{ nH}$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	11,8 12,4		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	2100 1500		A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0,160	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W/(m}\cdot\text{K)} / \lambda_{grease} = 1\text{ W/(m}\cdot\text{K)}$		R_{thCH}	0,0170		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

初步数据
Preliminary Data

二极管，制动-斩波器 / Diode, Brake-Chopper

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	600	V
连续正向直流电流 Continuous DC forward current		I_F	300	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	600	A
I_{2t} -值 I_{2t} - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{2t}	8400 7900	A^2s A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 300\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 300\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 300\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,55 1,50 1,45	1,95	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 300\text{ A}, -di_F/dt = 3300\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	190 235 250		A A A
恢复电荷 Recovered charge	$I_F = 300\text{ A}, -di_F/dt = 3300\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	13,0 24,0 28,0		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 300\text{ A}, -di_F/dt = 3300\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	3,40 6,20 7,00		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,320	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,0340		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

反向二极管 / Diode, Reverse

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	600	V
连续正向直流电流 Continuous DC forward current		I_F	300	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	600	A
I_{2t} -值 I_{2t} - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{2t}	8400 7900	A^2s A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 300\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 300\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 300\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,55 1,50 1,45	1,95	V V V
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,320	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,0340		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

初步数据
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		29,0 23,0	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		23,0 11,0	mm
相对电痕指数 Comperative tracking index		CTI	> 400	
杂散电感, 模块 Stray inductance module		L _{sCE}	min. 20	typ. max. nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC'+EE'}	0,70	mΩ
储存温度 Storage temperature		T _{stg}	-40	125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00	6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	2,5	- 5,0 Nm
重量 Weight		G	340	g

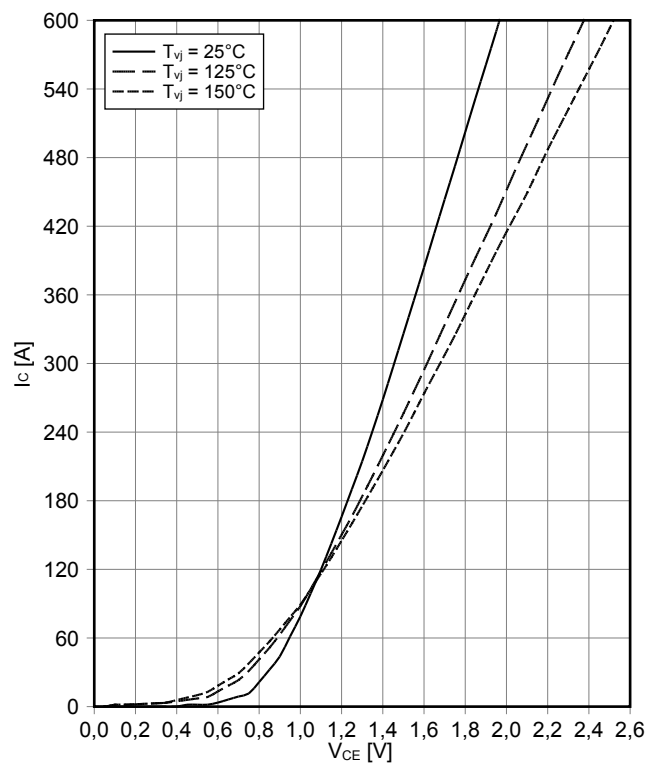
初步数据 Preliminary Data

输出特性 IGBT, 制动-斩波器 (典型)

output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$

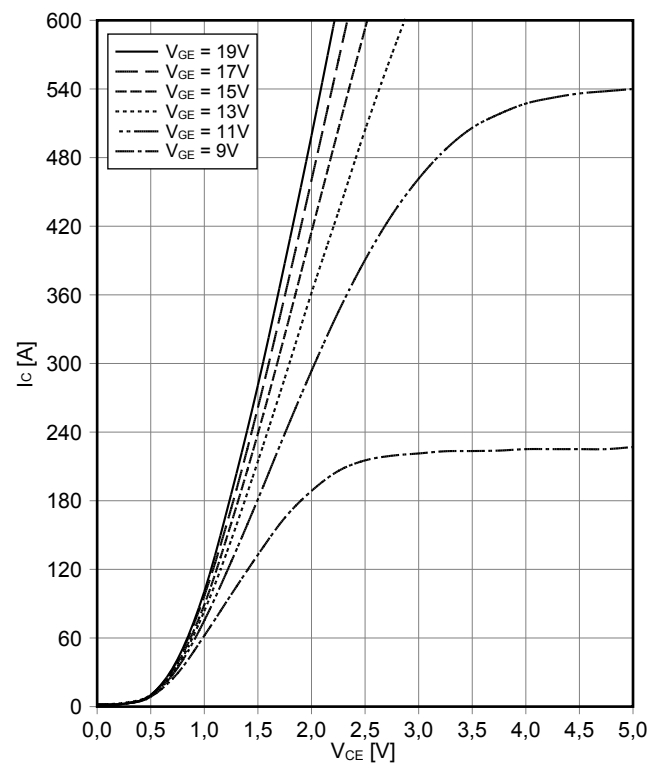


输出特性 IGBT, 制动-斩波器 (典型)

output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$

$T_{vj} = 150^\circ\text{C}$

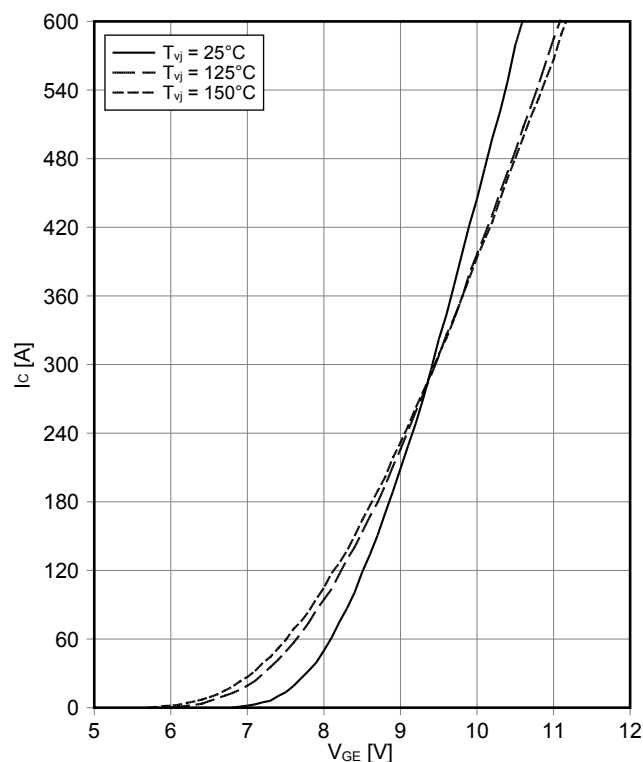


传输特性 IGBT, 制动-斩波器 (典型)

transfer characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{GE})$

$V_{CE} = 20\text{ V}$

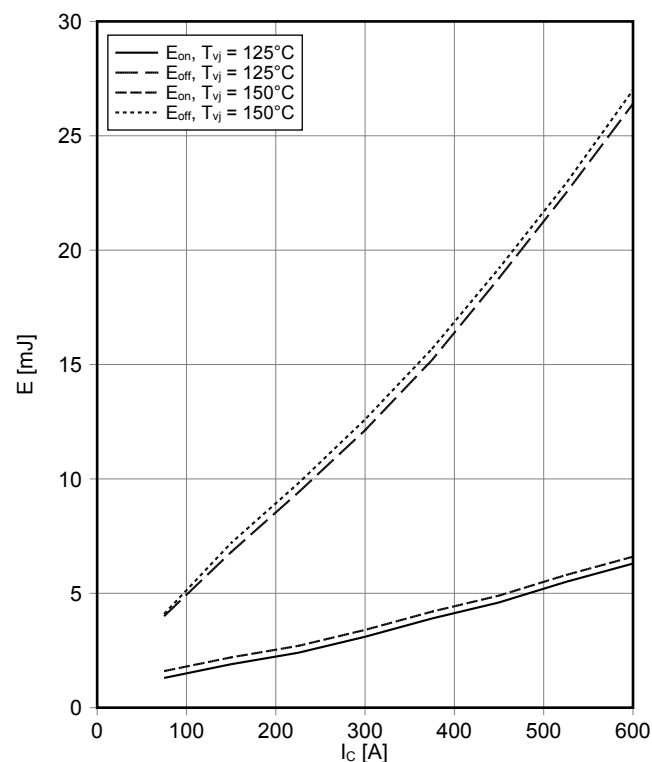


开关损耗 IGBT, 制动-斩波器 (典型)

switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$

$V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 2.4\ \Omega$, $R_{Goff} = 2.4\ \Omega$, $V_{CE} = 300\text{ V}$



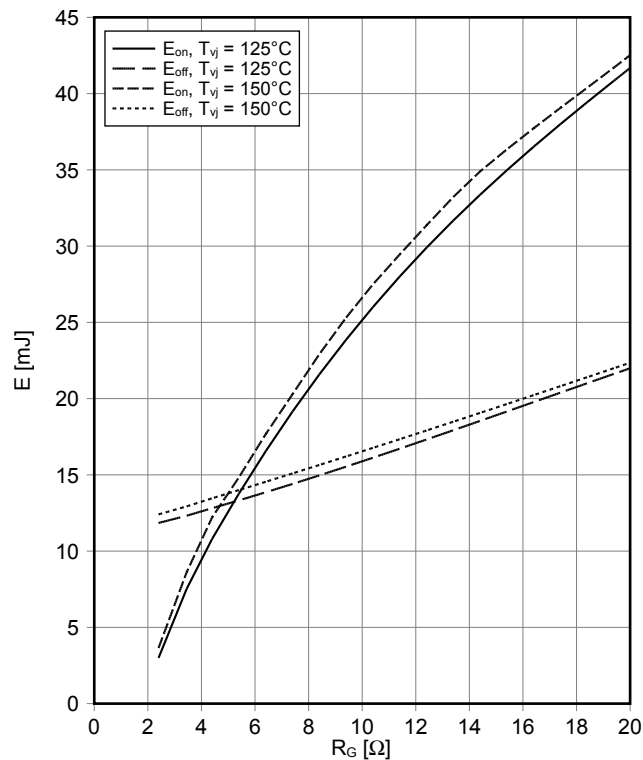
初步数据 Preliminary Data

开关损耗 IGBT, 制动-斩波器 (典型)

switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

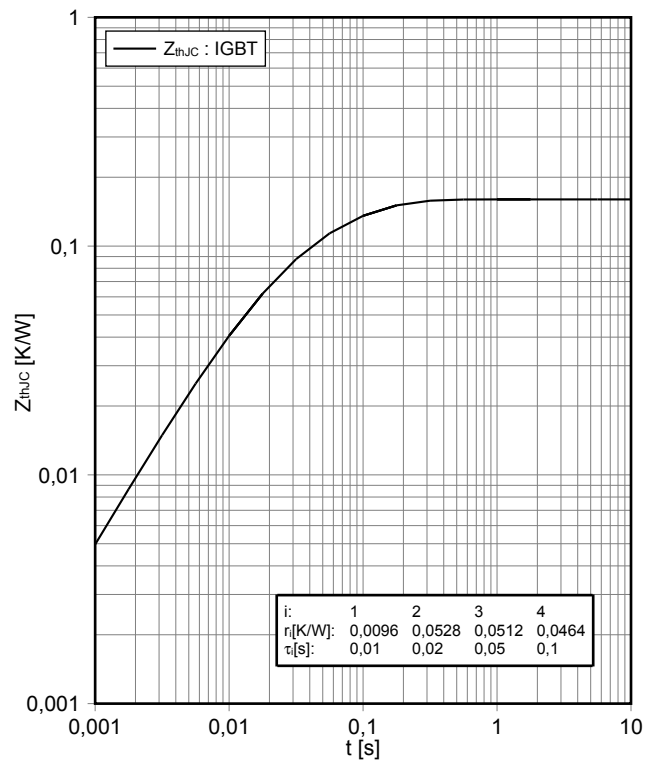
$V_{GE} = \pm 15\text{ V}$, $I_C = 300\text{ A}$, $V_{CE} = 300\text{ V}$



瞬态热阻抗 IGBT, 制动-斩波器

transient thermal impedance IGBT, Brake-Chopper

$Z_{thJC} = f(t)$

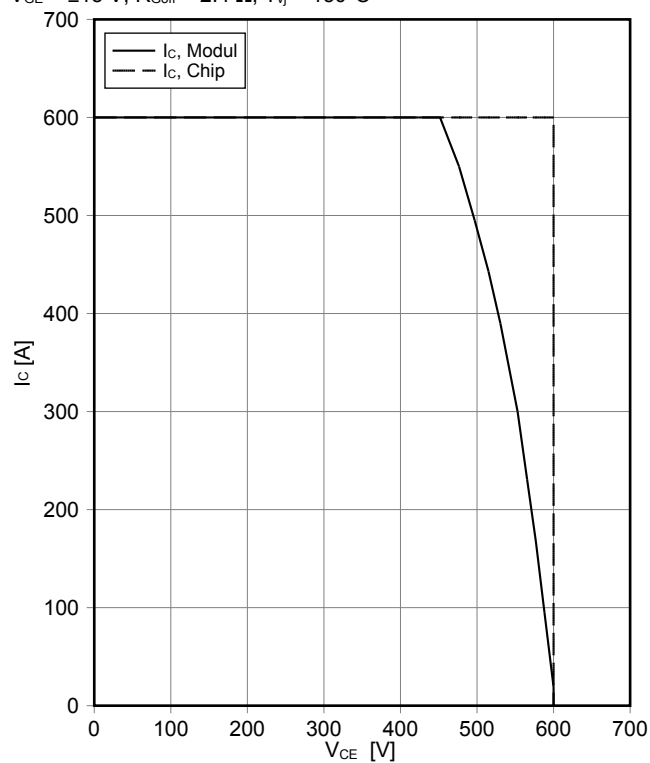


反偏安全工作区 IGBT, 制动-斩波器 (RBSOA)

reverse bias safe operating area IGBT, Brake-Chopper (RBSOA)

$I_C = f(V_{CE})$

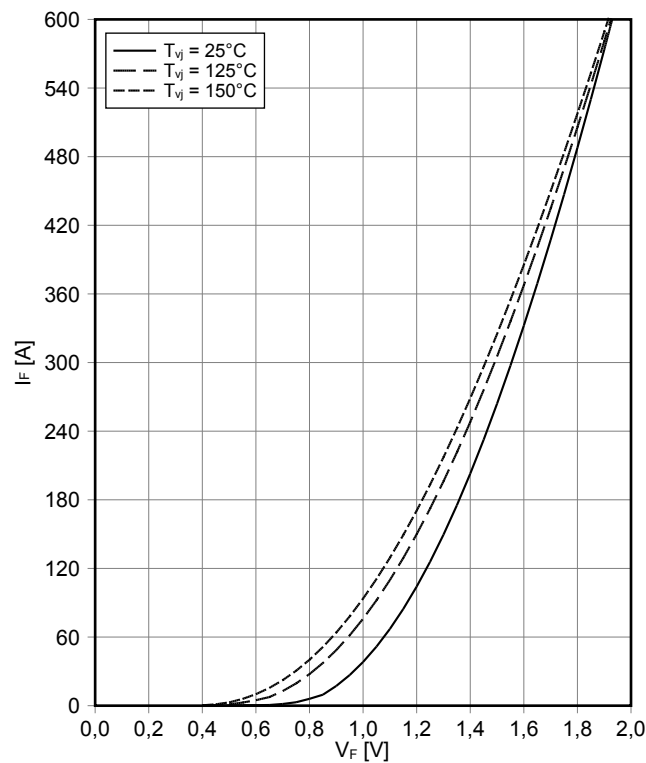
$V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 2.4\text{ }\Omega$, $T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 制动-斩波器 (典型)

forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



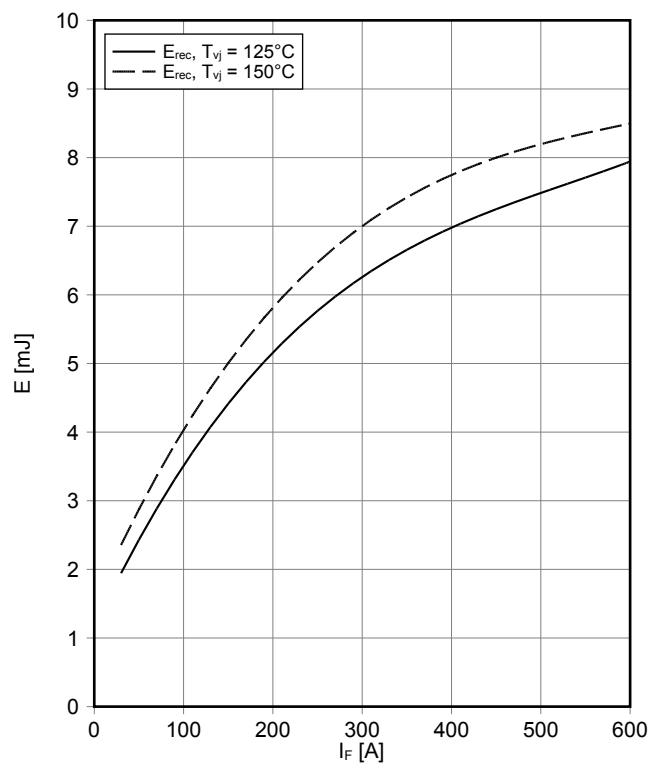
初步数据 Preliminary Data

开关损耗 二极管，制动-斩波器（典型）

switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(I_F)$

$R_{Gon} = 2.4 \Omega$, $V_{CE} = 300 \text{ V}$

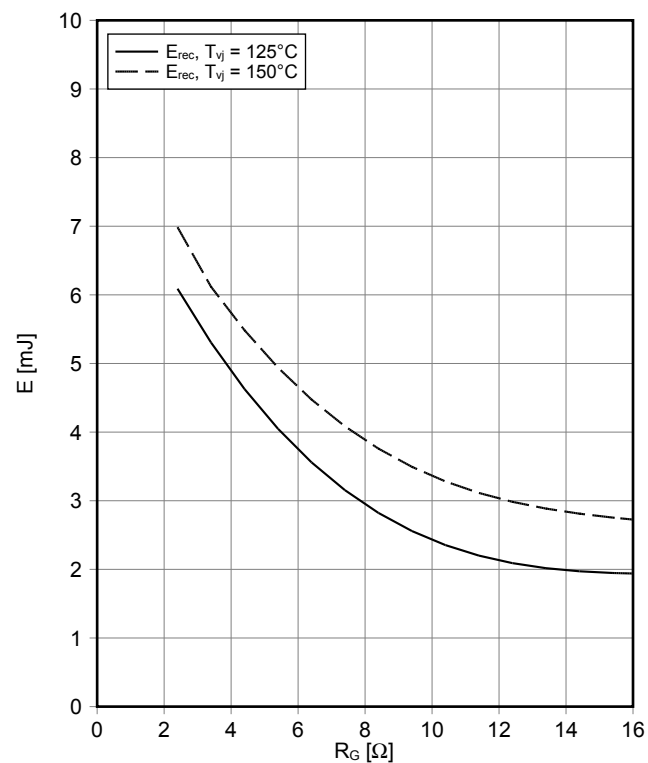


开关损耗 二极管，制动-斩波器（典型）

switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(R_G)$

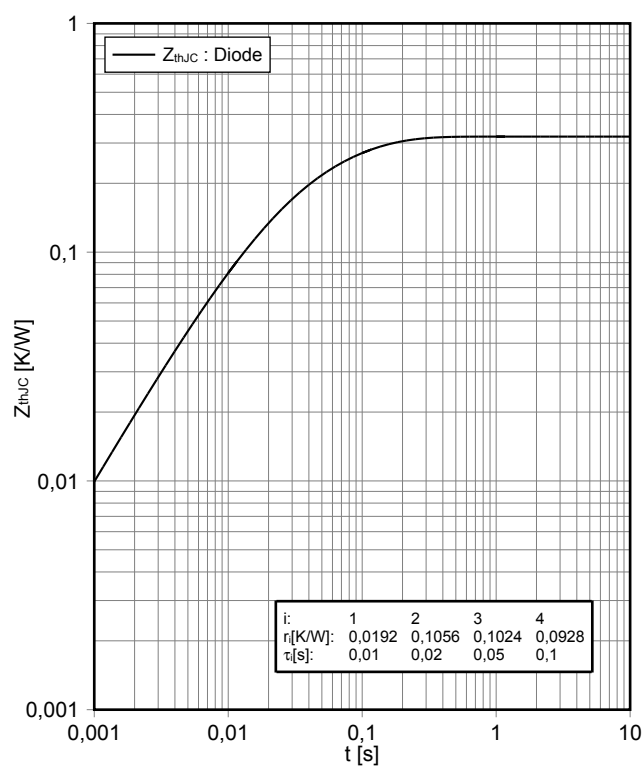
$I_F = 300 \text{ A}$, $V_{CE} = 300 \text{ V}$



瞬态热阻抗 二极管，制动-斩波器

transient thermal impedance Diode, Brake-Chopper

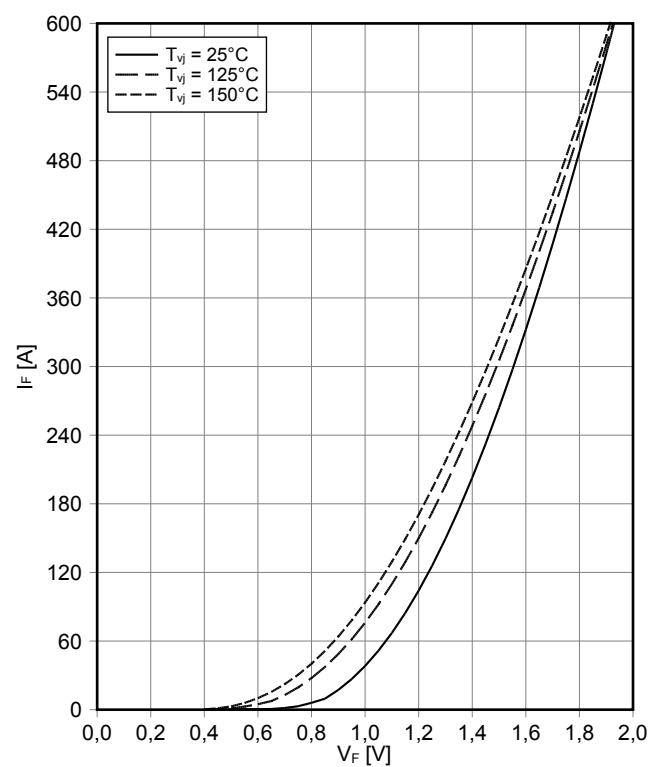
$Z_{thJC} = f(t)$



正向偏压特性 反向二极管（典型）

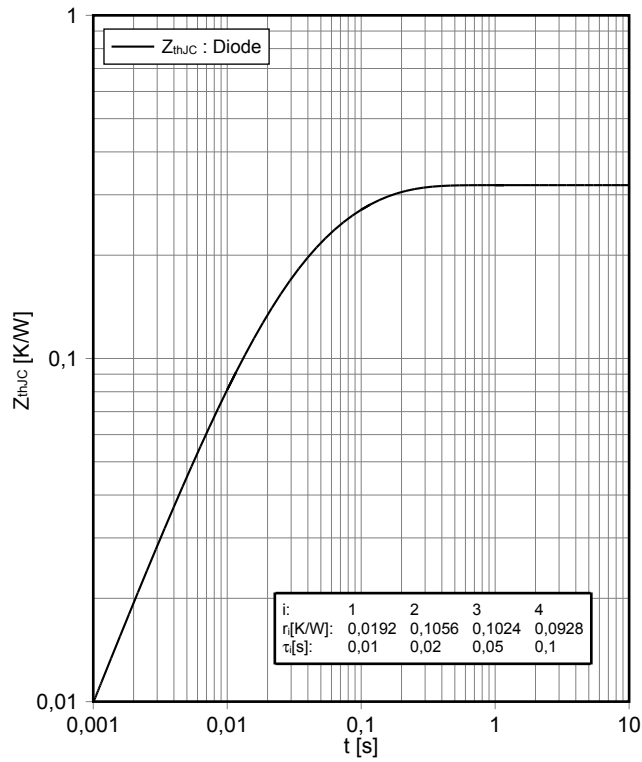
forward characteristic of Diode, Reverse (typical)

$I_F = f(V_F)$



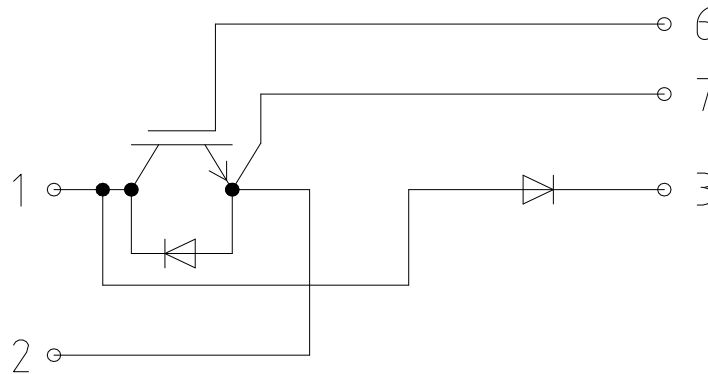
瞬态热阻抗 反向二极管

transient thermal impedance Diode, Reverse

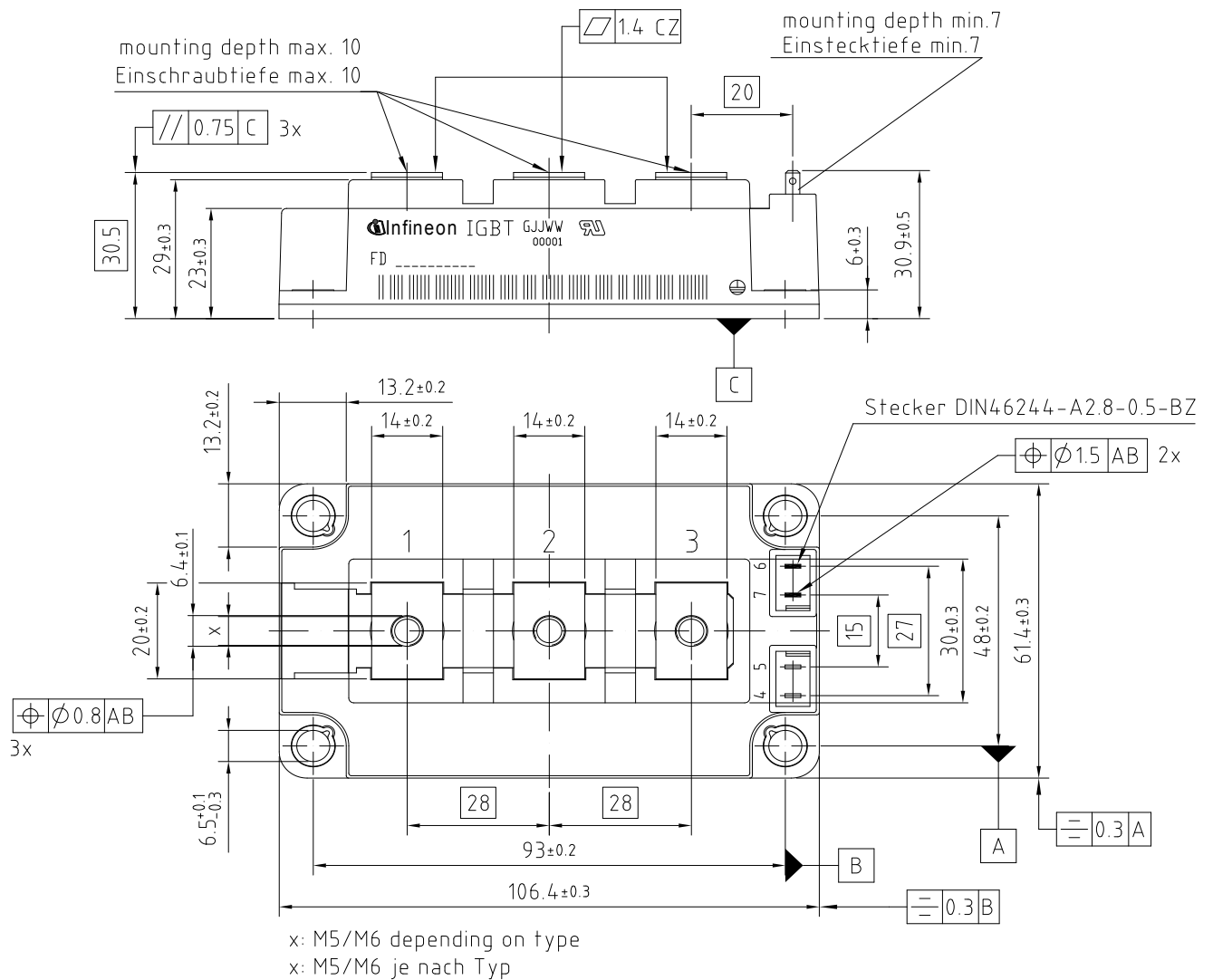
 $Z_{thJC} = f(t)$ 

接线图 / Circuit diagram

初步数据
Preliminary Data



封装尺寸 / Package outlines



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Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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